

**A STUDY OF Sn-Ag-Cu SOLDER
INTERCONNECTION BEHAVIOUR UNDER
GAMMA RADIATION EXPOSURE**

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**MASTER OF SCIENCE
(PHYSICS)**

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UNDER GAMMA RADIATION EXPOSURE**

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Thesis submitted to the Centre for Graduate Studies, Universiti Pertahanan Nasional
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(Physics)

ABSTRACT

The resilience of microelectronic packaging to gamma radiation is a crucial factor in solder joint evaluation due to its impact on the reliability of electronics within radiation-prone environments. This study focused on tin-silver copper (Sn96.5Ag3.0Cu0.5; SAC305) solder joints durability due to extreme gamma radiation environment. The SAC305 solder were exposed to gamma radiation with doses ranging from 5 to 50000 Gy. The evolution of the microstructure, intermetallic compound layer growth, crystallographic structure of solder alloy and behaviour of micromechanical properties of SAC305 solder joint due to gamma radiation exposure was investigated. The microstructure and IMC layer images were captured using optical microscope and then analysed by using ImageJ software. The micromechanical properties of solder joint such as the hardness, reduced modulus and creep behaviour was determined using nanoindentation testing and analysed using Oliver-Pharr Method. As the gamma radiation dose increased, the IMC layer thickness increases due to heat-induced coarsening behaviour. The XRD results show the presence of the β -Sn, Cu_6Sn_5 and Ag_3Sn phases. Micromechanical properties obtained from nanoindentation test indicated that the occurrence of wavy-pattern on the load-depth ($P-h$) curve. As radiation dose increased, the SAC305 solder transition from elastic to plastic. For the 0 Gy of SAC305 solder, the hardness and reduced modulus values were determined to be 0.26 GPa and 66.5 GPa, respectively. Prolonged exposure to gamma radiation leads to the coarsening of Ag_3Sn , diminishing the strengthening effect of the compound and increasing dislocation mobility. The eutectic phase area showed a parallel trend to the hardness value obtained. Overall, gamma radiation significantly

impacts microstructure, mechanical properties, and solder joint performance. Consideration of gamma radiation effects is essential in electronic package design for reliable operation in radiation-prone environments.

ABSTRAK

Ketahanan pempakejan mikroelektronik terhadap sinaran gama adalah faktor penting dalam penilaian sambungan pateri kerana kesannya terhadap kebolehharapan elektronik dalam persekitaran yang cenderung kepada sinaran. Kajian ini memberi tumpuan kepada ketahanan sambungan pateri timah-perak-kuprum ($\text{Sn}_{96.5}\text{Ag}_{3.0}\text{Cu}_{0.5}$; SAC305) terhadap persekitaran gama yang ekstrem. Sambungan pateri SAC305 telah terdedah kepada sinar gama dengan dos dari 5 hingga 50000 Gy. Evolusi mikrostruktur, pertumbuhan lapisan sebatian antara logam (IMC), struktur kristalografi aloi, dan tingkah laku sifat-sifat mikromekanikal sambungan pateri SAC305 disebabkan pendedahan kepada sinar gama telah diselidiki. Mikrostruktur dan imej lapisan IMC dicerap menggunakan mikroskop optik dan kemudian dianalisis dengan menggunakan perisian ImageJ. Sifat-sifat mikromekanikal sambungan pateri seperti kekerasan, modulus terkurang, dan rayapan ditentukan menggunakan ujian pelekukan nano dan dianalisis menggunakan kaedah Oliver-Pharr. Dengan peningkatan dos sinar gama, ketebalan lapisan IMC meningkat disebabkan oleh kelakuan pelembutan akibat haba. Keputusan XRD menunjukkan kehadiran fasa β -Sn, Cu_6Sn_5 , dan Ag_3Sn . Sifat-sifat mikromekanikal yang diperolehi daripada ujian pelekukan nano menunjukkan kehadiran corak bergelombang pada lengkung beban-kedalaman ($P-h$). Dengan peningkatan dos radiasi, sambungan pateri SAC305 berubah dari keadaan elastik kepada plastik. Bagi sambungan pateri SAC305 kawalan, nilai kekerasan dan modulus terkurang ditentukan masing-masing adalah 0.26 GPa dan 66.5 GPa. Pendedahan yang berpanjangan kepada sinar gama menyebabkan pelembutan Ag_3Sn , mengurangkan kesan penguatannya dan meningkatkan mobiliti kehelan.

Kawasan fasa eutektik menunjukkan trend yang selari dengan nilai kekerasan yang diperoleh. Secara keseluruhan, sinaran gama secara signifikan mempengaruhi mikrostruktur, sifat-sifat mekanikal, dan prestasi sambungan pateri. Pertimbangan kesan sinar gama adalah penting dalam reka bentuk pembungkusan elektronik untuk operasi yang boleh dipercayai dalam persekitaran cenderung radiasi.

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APPROVAL

The Examination Committee has met on **12 July 2024** to conduct the final examination of **Muhammad Nur Hisyam Bin Rosman** on his degree thesis entitled '**A Study Of Solder Interconnection Behaviour Under Gamma Radiation Exposure.**'.

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TABLE OF CONTENTS

	TITLE	PAGE
	ABSTRACT	ii
	ABSTRAK	iv
	ACKNOWLEDGEMENTS	vi
	APPROVAL	vii
	APPROVAL	viii
	DECLARATION OF THESIS	ix
	TABLE OF CONTENTS	x
	LIST OF TABLES	xii
	LIST OF FIGURES	xiii
	LIST OF ABBREVIATIONS	xix
	LIST OF SYMBOLS	xxi
CHAPTER 1	INTRODUCTION	23
	1.1 Background	23
	1.2 Problem Statement	25
	1.3 Objective	26
	1.4 Research Scope	26
	1.5 Significant of Research	27
CHAPTER 2	LITERATURE REVIEW	29
	2.1 Introduction	29
	2.2 Microelectronic Packaging and Interconnection	29
	2.3 Solder Materials and Soldering Process	31
	2.3.1 Lead-free solder	33
	2.3.2 Soldering Process	36
	2.4 Interaction of Gamma Radiation and Materials	38
	2.5 Effect of Gamma Radiation on Solder	43
	2.5.1 Microstructure	44
	2.5.2 Mechanical Properties	49
	2.6 Nanoindentation Approach	51
CHAPTER 3	RESEARCH METHODOLOGY	56
	3.1 Introduction	56
	3.2 Sample Preparation	58
	3.2.1 Sn-Ag-Cu	58
	3.2.2 Soldering Process	61
	3.3 Gamma Radiation Exposure	64
	3.4 Metallographic Technique	67
	3.4.1 Mounting	67
	3.4.2 Grinding	70
	3.4.3 Polishing	71

	3.4.4 Etching	72	
	3.5 Microstructure Observation Using Optical Microscope	74	
	3.6 Testing and Characterization	76	
	3.6.1 Physical Change	76	
	3.6.2 Nanoindentation Test	78	
	3.7 Summary	80	
CHAPTER 4	RESULTS AND DISCUSSIONS		81
	4.1 Results	81	
	4.2 Soldering Alloy and Soldering Process	82	
	4.3 Physical Characterization of SAC305 Solder	83	
	4.3.1 Microstructure Evolution	83	
	4.3.2 Intermetallic Compound Layer Thickness	91	
	4.3.3 X-Ray Diffractometer (XRD)	97	
	4.4 Micromechanical Properties of SAC305	104	
	4.4.1 Load Versus Depth	105	
	4.4.2 Hardness and Reduced Modulus	109	
	4.4.3 Stress Exponent	120	
	4.5 Correlation between Microstructural Behaviour and Micromechanical Properties	123	
CHAPTER 5	CONCLUSION AND RECOMMENDATIONS		128
	5.1 Conclusions	128	
	5.2 Recommendations	129	
	REFERENCES		131
	BIODATA OF STUDENT		142
	LIST OF PUBLICATIONS		143

LIST OF TABLES

TABLE NO.	TITLE	PAGE
Table 2.1	Effect of radiation on electronic materials and devices	42
Table 3.1	Exposure Time for Gamma Radiation	66
Table 4.1	Elemental percentage for SAC305 solder sample	86
Table 4.2	Volume fraction percentage and the average size of the near eutectic phase of SAC305 solder	89
Table 4.3	The value of IMC thickness of SAC305	93
Table 4.4	The micromechanical properties of 0 Gy and irradiated SAC solder	109

LIST OF FIGURES

FIGURE NO.	TITLE	PAGE
Figure 2.1	Solder joints in single chip and multichip (heterogeneous integration) packaging (Lau & Lee, 2020)	31
Figure 2.2	Types of solder form exist in the industry (Santosh, 2019)	32
Figure 2.3	Sn–Ag–Cu ternary phase diagram (Lehan <i>et. al.</i> , 2022)	36
Figure 2.4	Soldering reaction between molten solder and substrate (Vianco, 2017).	37
Figure 2.5	Typical reflow profile for reflow soldering (Tsai, 2012)	38
Figure 2.6	Schematic of atomic displacement damage in a crystalline solid. (a) Atomic displacement event. (b) Simple radiation-induced defects (vacancy and interstitial) (Maurer <i>et. al.</i> , 2008)	39
Figure 2.7	The radiation-induced defect mechanism (Ismail. <i>et. al.</i> , 2024)	40
Figure 2.8	Solder joint schematic diagram consists of solder bulk or solder matrix, IMC layer and substrate (Guo <i>et. al.</i> , 2023)	44
Figure 2.9	Representative of a) SnPb solder microstructure (Vianco <i>et. al.</i> , 2006) and b) Sn-Ag-Cu solder microstructure (Li <i>et. al.</i> , 2020)	45

Figure 2.10	Cu ₆ Sn ₅ IMC layer formed at the interfacial Sn-Ag-Cu and Cu substrate (Sayyadi & Naffakh-Moosavy, 2019)	46
Figure 2.11	Examples of micro-voids and microcracks in the solder joint are due to radiation (Guan <i>et. al.</i> , 2023)	48
Figure 2.12	Load-displacement nanoindentation curve	54
Figure 2.13	The SEM images of indenter tips commonly used in nanoindentation tests (a) Berkovich (b) Knoop (c) cube-corner (Fischer-Cripps, 2000)	54
Figure 3.1	Methodology Flow Chart	57
Figure 3.2	(a) The SAC305 solder paste, (b) the stencil, (c) the test board, and (d) the squeegee	59
Figure 3.3	Solder paste mixing process	59
Figure 3.4	(a) Stencil process (b) Schematic of stencil printing	60
Figure 3.5	The solder was pasted on the PCB board	61
Figure 3.6	The reflow soldering oven	62
Figure 3.7	The reflow profile	63
Figure 3.8	PCB board inside the reflow oven	63
Figure 3.9	Sawing Machine	64
Figure 3.10	The PCB that has been cut	64
Figure 3.11	Gamma cell gauge	66
Figure 3.12	The Gamma cell radiation chamber	66
Figure 3.13	The PCB piece was inserted vertically into the mould	68

Figure 3.14	Epoxy resin VersoCit-2 liquid and hardener VersoCit-2 Powder	68
Figure 3.15	Mixing of epoxy resin and hardener	69
Figure 3.16	Pouring process	69
Figure 3.17	Mounted sample	70
Figure 3.18	Grinder and Polisher machine	71
Figure 3.19	Optical Microscope	74
Figure 3.20	FESEM testing setup	75
Figure 3.21	Schematic diagram of IMC measurement	76
Figure 3.22	The schematic diagram of grain size measurement	77
Figure 3.23	The schematic diagram of Nanotest™	79
Figure 3.24	Schematic diagram illustrating the location of nanoindentation on the solder	80
Figure 4.1	(a) Solder paste on the top of PCB surface before reflow process (b) Solder on PCB after reflow soldering	82
Figure 4.2	The image of the mapping element of the SAC305 solder sample	83
Figure 4.3	FESEM mapping image of the (a) SAC305, (b) Sn element, (c) Ag element, and (d) Cu element	85
Figure 4.4	EDS Element Spectrum	85
Figure 4.5	Optical microscope images of SAC305 solder under variation doses of gamma radiation 0 Gy, 5 Gy, 50 Gy, 500 Gy, 5000 Gy and 50000 Gy	87

Figure 4.6	ImageJ analysis on SAC305 solder microstructure under gamma radiation of (a) 0 Gy, (b) 5 Gy, (c) 50 Gy, (d) 500 Gy (e) 5000 Gy and (f) 50000 Gy	88
Figure 4.7	Volume fraction percentage of eutectic phase area versus β -Sn area	88
Figure 4.8	Representative image of FESEM after exposure to gamma radiation shows the occurrence of microcracks on 5000 Gy	91
Figure 4.9	The IMC micrograph for (a) 0 Gy, (b) 5 Gy, (c) 50 Gy, (d) 500 Gy, (e) 5000 Gy, and (f) 50000 Gy	92
Figure 4.10	The IMC trace for (a) 0 Gy, (b) 5 Gy, (c) 50 Gy, (d) 500 Gy, (e) 5000 Gy, and (f) 50000 Gy	93
Figure 4.11	IMC layer thickness of 0 Gy and irradiated SAC305 solder joint	94
Figure 4.12	The percentage of the increment of IMC thickness	94
Figure 4.13	XRD pattern of SAC305 solder joints on selected gamma doses (a) 50000 Gy, (b) 5000 Gy, (c) 500 Gy, (d) 50 Gy, (e) 5 Gy and (f) 0 Gy	98
Figure 4.14	The dislocation density of both 220 and 240 β -Sn peaks under varied gamma radiation dose	99
Figure 4.15	Crystallite size (\AA) of both 220 and 240 β -Sn peaks under varied gamma radiation dose	100

Figure 4.16	Dislocation density of both 220 and 240 β -Sn peaks under varied gamma radiation dose	102
Figure 4.17	Lattice strain of both 220 and 240 β -Sn peaks under varied gamma radiation dose	103
Figure 4.18	The indentation position at the centre of the SAC305 solder	105
Figure 4.19	<i>P-h</i> curve of indentation of 0 Gy and irradiated SAC305 solder	106
Figure 4.20	The wavy curve (oval shape) and the arrow show elastic and plastic	107
Figure 4.21	Hardness of SAC305 solder joint under varied gamma radiation doses	111
Figure 4.22	Illustration of indentation response towards (a) non-irradiated solder joint (b) irradiated solder joint (Wan Yusoff <i>et. al.</i> , 2023)	114
Figure 4.23	Reduced modulus of SAC305 solder joint under varied gamma radiation doses	115
Figure 4.24	Maximum depth of SAC305 solder under variation of gamma doses	116
Figure 4.25	Maximum depth versus hardness of SAC305 solder joint under varied gamma radiation doses.	117
Figure 4.26	Hardness values and plastic work of SAC305 solder under variation gamma doses	118

Figure 4.27	Reduced modulus values and elastic work of SAC305 solder under variation gamma doses	119
Figure 4.28	Depth versus dwell time	121
Figure 4.29	Log Strain versus Log Stress	121
Figure 4.30	Stress exponent (n) of SAC305 solder joint under varied gamma radiation doses	123

LIST OF ABBREVIATIONS

Ag	-	Argentum
Au	-	Gold
Au-Sn	-	Gold-Tin
BGA	-	Ball Grid Array
Bi	-	Bismuth
Cd	-	Cadmium
Cu	-	Copper
Co-60	-	Cobalt-60
DSC	-	Differential Scanning Calorimetry
EDS	-	Energy Dispersive X-ray Spectroscopy
EMR	-	Electromagnetic Radiation
FESEM	-	Field Emission Scanning Electron Microscopy
FIB	-	Focussed Ion Beam
Ge	-	Germanium
HCl	-	Hydrochloric acid
hrs	-	hours
HRTEM	-	High-resolution Transmission Electron Microscopy
IMC	-	Intermetallic Compound
In	-	Indium
IPC	-	Institute for Printed Circuits
min	-	minute
PCB	-	Printed Circuit Board
<i>P-h</i>	-	Load-depth
PTH	-	Plated through-hole
Pu	-	Plutonium
Ra	-	Radium
RoHS	-	Restriction of Hazardous Substances
s	-	second

Sb	-	Antimony
SiC	-	Silicon Carbide
SMT	-	Surface Mount Technology
Sn-Ag-Cu, SAC	-	Tin-Silver-Copper
Sn-Cu	-	Tin-Copper
Sn-Pb	-	Tin-Lead
SVPC	-	Solder Value Product Council
TGA	-	Thermogravimetric Analysis
Th	-	Thorium
U	-	Uranium
WEE	-	Waste Electrical and Electronic Equipment Directive
XRD	-	X-Ray Diffraction

LIST OF SYMBOLS

A	-	dose rate
A_c	-	projected contact area
A_o	-	initial activity
α	-	alpha
β	-	Beta
c	-	speed of light
$^{\circ}C$	-	Celsius
d	-	d-spacing
dh	-	change of displacement
dP	-	change of load
E	-	reduced modulus
E_i	-	reduced elastic modulus
E_r	-	initial elastic reduced modulus
e	-	indenter geometry
$e+$	-	Proton
$e-$	-	Electron
H	-	Hardness
h	-	depth
h_c	-	contact depth
h_f	-	final displacement
h_s	-	Stiffness displacement
h_{max}	-	maximum depth
$h\nu$	-	energy of directional photon
$h\nu'$	-	energy of scattering photon
m_0c^2	-	rest mass of electron
n	-	poisson's ratio
P	-	Load
P_{max}	-	contact depth
S	-	Stiffness

s	-	Second
T	-	Temperature
t	-	Time
$t_{1/2}$	-	half life
v	-	Velocity
ν_i	-	poisson's ratio for indenter
γ	-	gamma radiation
λ	-	Wavelength
θ	-	Angle
$^{\circ}$	-	Degree

CHAPTER 1

INTRODUCTION

1.1 Background

The durability and reliability of interconnection in electronic packaging is very important especially when it is applied to satellites, spacecraft, biomedical or nuclear power devices since this equipment ordinarily interacts with ionizing radiation such as high energy cosmic, neutron and gamma rays. Ionizing radiation has enough energy to alter the properties of the material by breaking its chemical bond will cause degradation and displacement damage. Therefore, the assessment of its mechanical, and physical properties and microstructural study at the atomic level such as dislocation movements and solder interconnection behaviour are vital to prevent the failure in electronic packaging.

Application of microelectronics packages covers almost all areas of application including radiation-related industries such as radiography used in medical and health sciences; and non-destructive testing. According to Arshak *et. al.*, (2004), exposure to ionizing radiation can occur in various occupational environments such as educational institutes, research establishments and medical institutions. Gamma radiation, a form of ionizing radiation, is denoted by γ . This electromagnetic radiation consists of

packets of photons, which are massless particles with very high frequencies and very short wavelengths. Yannakopoulos *et. al.*, (2008) mentioned that the effects of radiation on matter could be grouped into atomic displacement, production of impurities and ionization. Ray (2023) reported that electronic solid-state devices experience displacement damage of solder after exposed to radiation. Some of these radiation effects may lead to changes in terms of the physical and chemical properties of the substance. Irradiation on electronic material may degrade the device's performance (Arshak *et. al.*, 2004) and also alter the internal structure of the materials and therefore their mechanical and chemical properties (Stiegler *et. al.*, 1979). Previous studies showed that package material can be affected by gamma radiation (Jalar *et. al.*, 2014; Yusoff *et. al.*, 2011). In satellite sensor applications, microelectronic packages are embedded in sensor devices. These devices may be exposed to high levels of gamma radiation. Sensors may be affected by prolonged exposure to ionizing radiation such as gamma rays. The results from these studies may lead to improvement in material selection and the design of microelectronic packages. Earlier studies have investigated the effects of radiation on the solder joint, microelectronic packages and devices (Wen *et. al.*, 2020; Wang *et. al.*, 2018; Gong *et. al.*, 2017; Arutt *et. al.*, 2016; Jalar *et. al.*, 2012). Yusoff *et. al.*, (2014) found that exposure to Co-60 gamma radiation-induced dislocation of atomic arrangement on gold ball bond. According to Abdul Amir *et. al.*, (2009), the occurrence of atomic displacement on the silicon metal oxide semiconductor due to ionizing radiation has decreased the reliability of the sample. The subthreshold irradiation plays an important role in the microstructure evolution and defects migration on irradiated ceramics (Zinkle and Kinoshita 1997). However, the study on the durability and reliability of interconnect materials especially solder joints (for extraordinary applications) such as